

BRCS120P03YB

Rev.B Oct.-2024

/ Descriptions

PDFN 3×3A-8L P MOS

P-Channel Enhancement Mode Field Effect Transistor in a PDFN3×3A-8L Plastic Package.

/ Features

$V_{DS} (V) = -30V$

$I_D = -35 A (V_{GS} = \pm 20V)$

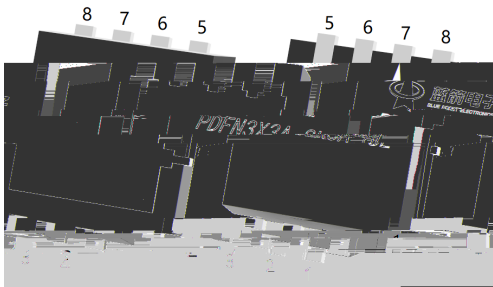
$R_{DS(ON)}@10V \ 12mR(Typ.10mR)$

HF Product.

/ Applications

DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.



/ Marking

See Marking Instructions.

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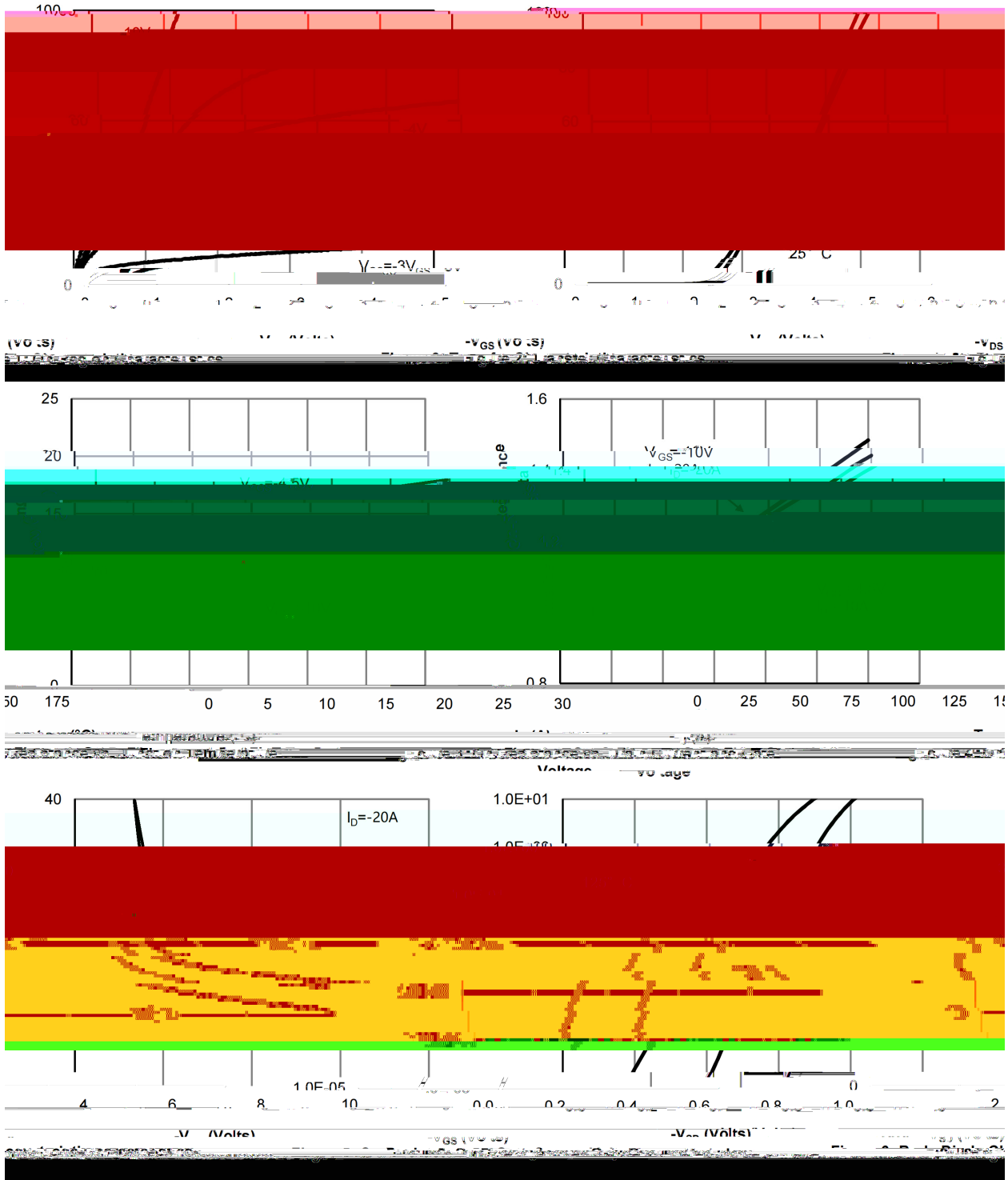


DATA SHEET

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-30	V
Drain Current	$I_D(T_C=25^\circ\text{C})$		

Parameter	Symbol
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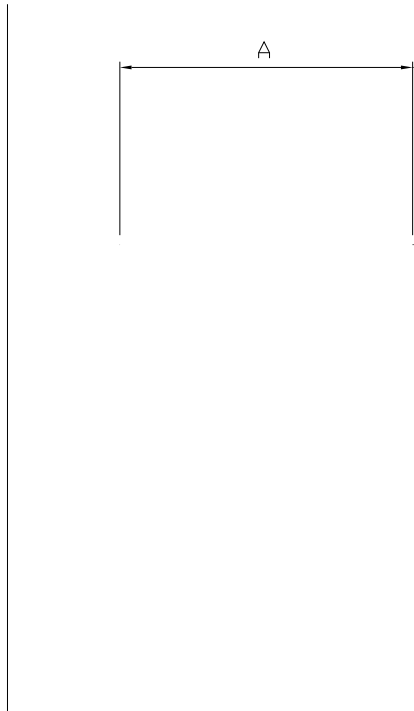
/ Electrical Characteristic Curve



/ Package Dimensions

PDFN3X3A-8L

Unit:mm



Dimensions In Millimeterer			
Symbol	MIN	TYP	MAX
A	3.20	3.30	3.40
A1	3.10	3.15	3.20
B	3.20	3.30	3.40
B1	2.95	3.00	3.05

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() / Temperature Profile for IR Reflow Soldering(Pb-Free)
